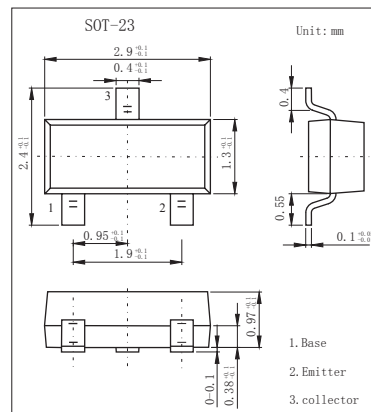


PNP Transistors

KST8550S



■ Features

- Collector current: $I_c = -0.5A$

■ Absolute Maximum Ratings $T_a = 25^\circ C$

| Parameter | Symbol | Rating | Unit |
|-------------------------------|-----------|------------|------------|
| Collector-Base Voltage | V_{CBO} | -40 | V |
| Collector-Emitter Voltage | V_{CEO} | -25 | V |
| Emitter-Base Voltage | V_{EBO} | -5 | V |
| Collector Current -Continuous | I_c | -0.5 | A |
| Collector Power Dissipation | P_c | 0.3 | W |
| Junction Temperature | T_j | 150 | $^\circ C$ |
| Storage Temperature | T_{stg} | -55 to 150 | $^\circ C$ |

■ Electrical Characteristics $T_a = 25^\circ C$

| Parameter | Symbol | Testconditions | Min | Typ | Max | Unit |
|--------------------------------------|---------------|--|-----|-----|------|---------|
| Collector-base breakdown voltage | V_{CBO} | $I_c = -100 \mu A, I_E = 0$ | -40 | | | V |
| Collector-emitter breakdown voltage | V_{CEO} | $I_c = -1mA, I_B = 0$ | -25 | | | V |
| Emitter-base breakdown voltage | V_{EBO} | $I_E = -100 \mu A, I_c = 0$ | -5 | | | V |
| Collector cut-off current | I_{CBO} | $V_{CB} = -40V, I_E = 0$ | | | -0.1 | μA |
| Collector cut-off current | I_{CEO} | $V_{CE} = -20V, I_B = 0$ | | | -0.1 | μA |
| Emitter cut-off current | I_{EBO} | $V_{EB} = -3V, I_c = 0$ | | | -0.1 | μA |
| DC current gain | h_{FE} | $V_{CE} = -1V, I_c = -50mA$ | 120 | | 400 | |
| | | $V_{CE} = -1V, I_c = -500mA$ | 50 | | | |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_c = -500mA, I_B = -50mA$ | | | -0.5 | V |
| Base-emitter saturation voltage | $V_{BE(sat)}$ | $I_c = -500mA, I_B = -50mA$ | | | -1.2 | V |
| Transition frequency | f_T | $V_{CE} = -6V, I_c = -20mA, f = 30MHz$ | 150 | | | MHz |

■ Classification of $h_{FE}(1)$

| Marking | 2TY | | | |
|---------|---------|---------|---------|---------|
| Rank | | L | H | J |
| Range | 200-350 | 120-200 | 144-202 | 300-400 |

KST8550S

Typical Characteristics

